8-pin SOIC Single-Channel Phototransistor Output Optocoupler



Description

These devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector, in a surface mountable, small outline, plastic package. They are ideally suited for high-density applications, and eliminate the need for through-the-board mounting.

Features

- Closely Matched Current Transfer Ratios Minimum BV_{CEO} of 70 V Guaranteed
 - ◆ MOC205M, MOC206M, MOC207M
- Minimum BV_{CEO} of 30 V Guaranteed
 - ◆ MOC211M, MOC212M, MOC213M, MOC216M, MOC217M
- Low LED Input Current Required for Easier Logic Interfacing
 - MOC216M, MOC217M
- Convenient Plastic SOIC-8 Surface Mountable Package Style, with 0.050" Lead Spacing
- Safety and Regulatory Approvals:
 - ◆ UL1577, 2,500 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage
- These are Pb-Free Devices

Applications

- Feedback Control Circuits
- Interfacing and Coupling Systems of Different Potentials and Impedances
- General Purpose Switching Circuits
- Monitor and Detection Circuits



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SOIC8 CASE 751DZ

MARKING DIAGRAM



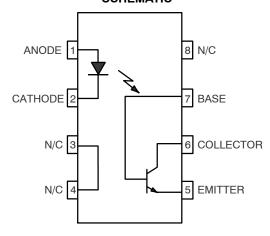
XXX = Specific Device Code

V = DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)

X = Year Code YY = Work Week

S = Assembly Package Code

SCHEMATIC



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

SAFETY AND INSULATION RATINGS (As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.)

Parameter		Characteristics
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains	<150 V _{RMS}	I–IV
Voltage	<300 V _{RMS}	I–III
Climatic Classification	55/100/21	
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V _{PR}	Input–to–Output Test Voltage, Method A, V_{IORM} x 1.6 = V_{PR} , Type and Sample Test with t_m = 10 s, Partial Discharge < 5 pC	904	V _{peak}
	Input–to–Output Test Voltage, Method B, V_{IORM} x 1.875 = V_{PR} , 100% Production Test with t_m = 1 s, Partial Discharge < 5 pC	1060	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	565	V_{peak}
V _{IOTM}	Highest Allowable Over-Voltage	4000	V _{peak}
	External Creepage	≥4	mm
	External Clearance	≥4	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥0.4	mm
T _S	Case Temperature (Note 1)	150	°C
I _{S,INPUT}	Input Current (Note 1)	200	mA
P _{S,OUTPUT}	Output Power (Note 1)	300	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	>10 ⁹	Ω

^{1.} Safety limit values – maximum values allowed in the event of a failure.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Rating	Value	Unit
TOTAL DI	EVICE	•	
T _{STG}	Storage Temperature	-40 to +125	°C
T _A	Ambient Operating Temperature	-40 to +100	°C
TJ	Junction Temperature	-40 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 seconds	°C
P_{D}	Total Device Power Dissipation @ T _A = 25°C	240	mW
	Derate above 25°C	2.94	mW/°C
EMITTER			
I _F	Continuous Forward Current	60	mA
I _F (pk)	Forward Current – Peak (PW = 100 μs, 120 pps)	1.0	Α
V _R	Reverse Voltage	6.0	V
P_{D}	LED Power Dissipation @ T _A = 25°C	90	mW
	Derate above 25°C	0.8	mW/°C
DETECTO	OR .		
I _C	Continuous Collector Current	150	mA
V_{CEO}	Collector-Emitter Voltage	30	V
V _{ECO}	Emitter-Collector Voltage	7	V
P_{D}	Detector Power Dissipation @ T _A = 25°C	150	mW
	Derate above 25°C	1.76	mW/°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Para	meter	Test Condition	Min	Тур	Max	Unit
EMITTER							
	Input Forward Voltage	MOC216M, MOC217M	I _F = 1 mA	-	1.07	1.3	V
V _F		MOC205M, MOC206M, MOC207M MOC211M, MOC212M, MOC213M	I _F = 10 mA	=	1.15	1.5	V
I _R	Reverse Leakage Current		V _R = 6 V	-	0.001	100	μΑ
C _{IN}	Input Capacitance			_	18	-	pF
DETECTOR	1						
I _{CEO1}	Collector-Emitter Dark Current		V _{CE} = 10 V, T _A = 25°C	_	1.0	50	nA
I _{CEO2}			V _{CE} = 10 V, T _A = 100°C	-	1.0	_	μΑ
BV _{CEO}	Collector-Emitter Breakdown Voltage	MOC205M, MOC206M, MOC207M	I _C = 100 μA	70	100	-	V
		MOC211M, MOC212M, MOC213M, MOC216M, MOC217M	I _C = 100 μA	30	100	-	V
BV _{CBO}	Collector-Base Breakdown	Voltage	I _C = 10 μA	70	120	_	V
BV _{ECO}	Emitter-Collector Breakdov	vn Voltage	I _E = 100 μA	7	10	_	V
C _{CE}	Collector-Emitter Capacita	nce	f = 1.0 MHz, V _{CE} = 0 V	-	7	_	pF
COUPLED				-			•
CTR	Collector-Output Current	MOC205M	I _F = 10 mA, V _{CE} = 10 V	40	-	80	%
		MOC206M	I _F = 10 mA, V _{CE} = 10 V	63	-	125	%
		MOC207M	I _F = 10 mA, V _{CE} = 10 V	100	-	200	%
		MOC211M	I _F = 10 mA, V _{CE} = 10 V	20	-	-	%
		MOC212M	I _F = 10 mA, V _{CE} = 10 V	50	-	-	%
		MOC213M	I _F = 10 mA, V _{CE} = 10 V	100	-	-	%
		MOC216M	I _F = 1 mA, V _{CE} = 5 V	50	-	-	%
		MOC217M	I _F = 1 mA, V _{CE} = 5 V	100	-	-	%
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	MOC205M, MOC206M, MOC207M MOC211M, MOC212M, MOC213M	I _C = 2 mA, I _F = 10 mA	-	_	0.4	V
		MOC216M, MOC217M	$I_C = 100 \mu A, I_F = 1 \text{ mA}$	-	-	0.4	V
t _{on}	Turn-On Time		I_C = 2 mA, V_{CC} = 10 V, R_L = 100 Ω (Figure 12)	-	7.5	-	μs
t _{off}	Turn-Off Time		I_C = 2 mA, V_{CC} = 10 V, R_L = 100 Ω (Figure 12)	_	5.7	-	μs
t _r	Rise Time		I_C = 2 mA, V_{CC} = 10 V, R_L = 100 Ω (Figure 12)	-	3.2	-	μs
t _f	Fall Time		$I_C = 2$ mA, $V_{CC} = 10$ V, $R_L = 100 \Omega$ (Figure 12)	-	4.7	_	μs
ISOLATION	CHARACTERISTICS						
V _{ISO}	Input-Output Isolation Voltage		t = 1 Minute	2500	-	-	VAC _{RMS}
C _{ISO}	Isolation Capacitance		V _{I-O} = 0 V, f = 1 MHz	-	0.2	-	pF
R _{ISO}	Isolation Resistance		V _{I-O} = ±500 VDC, T _A = 25°C	10 ¹¹	-	-	Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CURVES

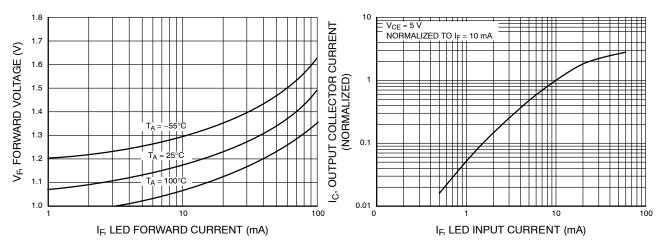


Figure 1. LED Forward Voltage vs. Forward Current

Figure 2. Output Current vs. Input Current

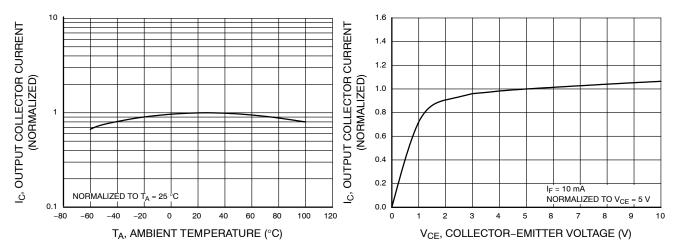


Figure 3. Output Current vs. Ambient Temperature

Figure 4. Output Current vs. Collector-Emitter Voltage

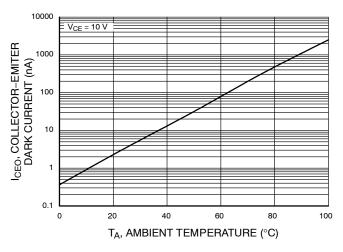


Figure 5. Dark Current vs. Ambient Temperature

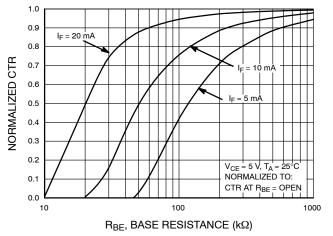
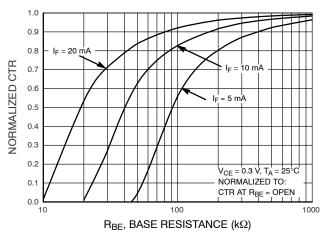


Figure 6. CTR vs. RBE (Unsaturated)

TYPICAL PERFORMANCE CURVES (continued)



V_{CC} = 10 V $I_C = 2 \text{ mA}$ 3.5 R_L = 100 Ω NORMALIZED TO: 3.0 NORMALIZED 2.5 2.0 1.5 1.0 0.5 0.0 0.01 100 R_{BE} , BASE RESISTANCE (M Ω)

Figure 7. CTR vs. R_{BE} (Saturated)

Figure 8. Normalized t_{on} vs. R_{BE}

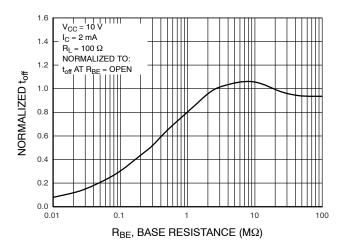


Figure 9. Normalized toff vs. RBE

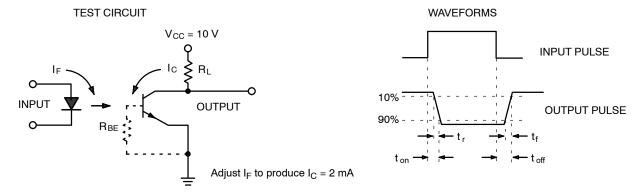


Figure 10. Switching Time Test Circuit and Waveforms

REFLOW PROFILE

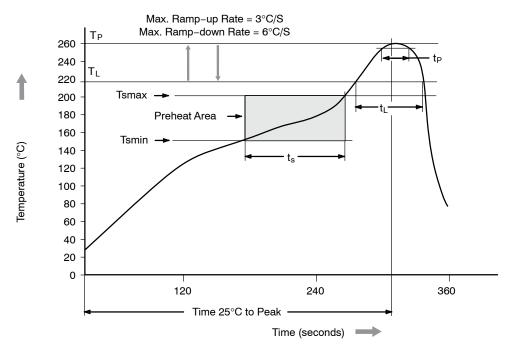


Figure 11. Reflow Profile

Table 1.

Profile Freature	Pb-Free Assembly Profile
Temperature Minimum (Tsmin)	150°C
Temperature Maximum (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60 – 120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second maximum
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / –5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second maximum
Time 25°C to Peak Temperature	8 minutes maximum

ORDERING INFORMATION (Note 2)

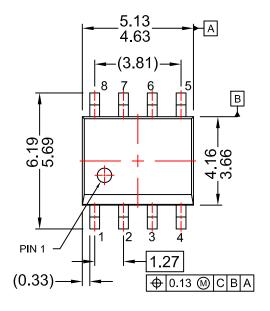
Part Number	Package	Shipping [†]
MOC205M	Small Outline 8-Pin	100 Units / Tube
MOC205R2M	Small Outline 8-Pin	2500 / Tape & Reel
MOC205VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	100 Units / Tube
MOC205R2VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	2500 / Tape & Reel

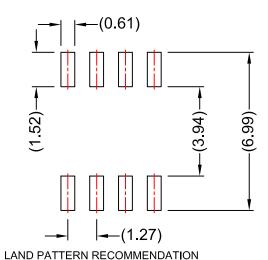
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{2.} The product orderable part number system listed in this table also applies to the MOC20XM and MOC21XM products.

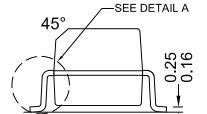
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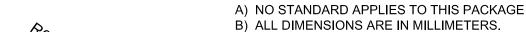


C O.10 C 0.53 3.63 MAX-0.20 0.08 0.28 8X



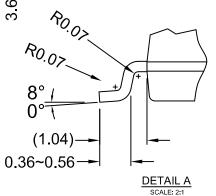
END VIEW

NOTES:



C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.

D) LANDPATTERN STANDARD: SOIC127P600X175-8M.



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